

**Triacs  
logic level**

**BT137 series D**

**GENERAL DESCRIPTION**

Glass passivated, sensitive gate triacs in a plastic envelope, intended for use in general purpose bidirectional switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

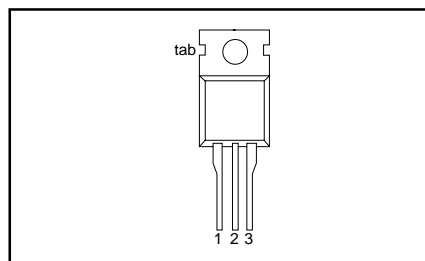
**QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
$V_{DRM}$	Repetitive peak off-state voltages	<b>500D</b> 500	<b>600D</b> 600	V
$I_{T(RMS)}$	RMS on-state current	8	8	A
$I_{TSM}$	Non-repetitive peak on-state current	65	65	A

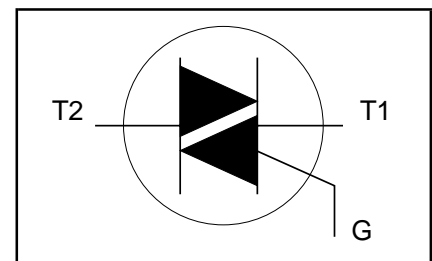
**PINNING - TO220AB**

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

**PIN CONFIGURATION**



**SYMBOL**



**LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
				-500 500 <sup>1</sup>	-600 600 <sup>1</sup>	
$V_{DRM}$	Repetitive peak off-state voltages		-	-500 500 <sup>1</sup>	-600 600 <sup>1</sup>	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 102^\circ\text{C}$	-	8		A
$I_{TSM}$	Non-repetitive peak on-state current	full sine wave; $T_j = 25^\circ\text{C}$ prior to surge $t = 20\text{ ms}$	-	65		A
		$t = 16.7\text{ ms}$	-	71		A
		$t = 10\text{ ms}$	-	21		A <sup>2</sup> s
$I^2t$	$I^2t$ for fusing		-			
$di_T/dt$	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 12\text{ A}$ ; $I_G = 0.2\text{ A}$ ; $di_G/dt = 0.2\text{ A}/\mu\text{s}$	-			
		T2+ G+	-	50		A/ $\mu\text{s}$
		T2+ G-	-	50		A/ $\mu\text{s}$
		T2- G-	-	50		A/ $\mu\text{s}$
		T2- G+	-	10		A/ $\mu\text{s}$
$I_{GM}$	Peak gate current		-	2		A
$V_{GM}$	Peak gate voltage		-	5		V
$P_{GM}$	Peak gate power		-	5		W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5		W
$T_{stg}$	Storage temperature		-40	150		$^\circ\text{C}$
$T_j$	Operating junction temperature		-	125		$^\circ\text{C}$

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/ $\mu\text{s}$ .

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## THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	full cycle	-	-	2.0	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	half cycle in free air	-	-	2.4	K/W
			-	60	-	K/W

## STATIC CHARACTERISTICS

 $T_j = 25\text{ }^\circ\text{C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{GT}$	Gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$				
		T2+ G+	-	2.5	5	mA
		T2+ G-	-	3.5	5	mA
		T2- G-	-	3.5	5	mA
		T2- G+	-	6.5	10	mA
$I_L$	Latching current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$				
		T2+ G+	-	1.6	15	mA
		T2+ G-	-	8.5	20	mA
		T2- G-	-	1.2	15	mA
		T2- G+	-	2.5	20	mA
$I_H$	Holding current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	1.5	10	mA
$V_T$	On-state voltage	$I_T = 10\text{ A}$	-	1.3	1.65	V
$V_{GT}$	Gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	-	0.7	1.5	V
$I_D$	Off-state leakage current	$V_D = 400\text{ V}; I_T = 0.1\text{ A}; T_j = 125\text{ }^\circ\text{C}$	0.25	0.4	-	V
		$V_D = V_{DRM(max)}; T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA

## DYNAMIC CHARACTERISTICS

 $T_j = 25\text{ }^\circ\text{C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$dV_D/dt$	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125\text{ }^\circ\text{C};$ exponential waveform; $R_{GK} = 1\text{ k}\Omega$	-	5	-	V/ $\mu\text{s}$
$t_{gt}$	Gate controlled turn-on time	$I_{TM} = 12\text{ A}; V_D = V_{DRM(max)}; I_G = 0.1\text{ A};$ $di_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	$\mu\text{s}$

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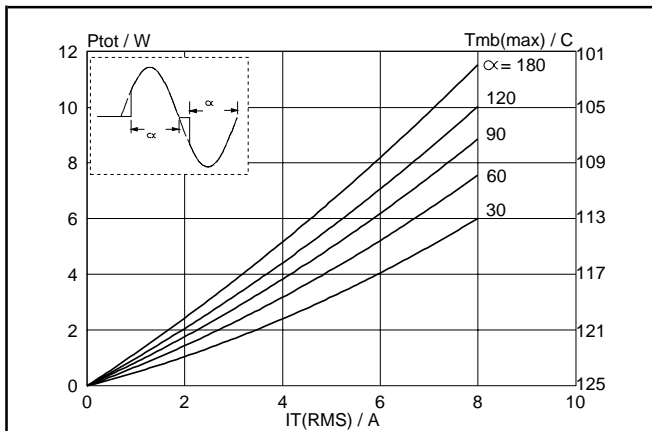


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha =$  conduction angle.

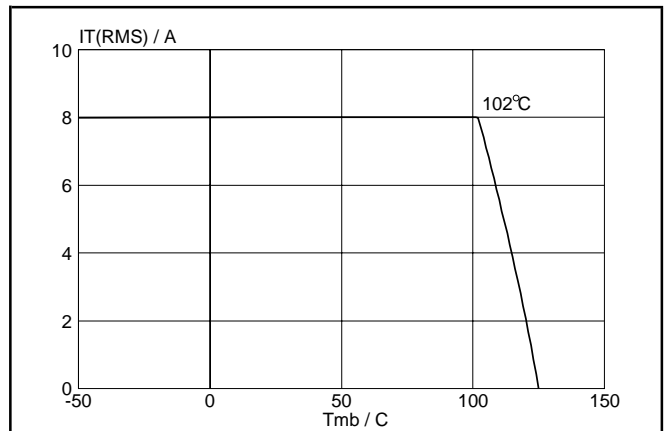


Fig.4. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

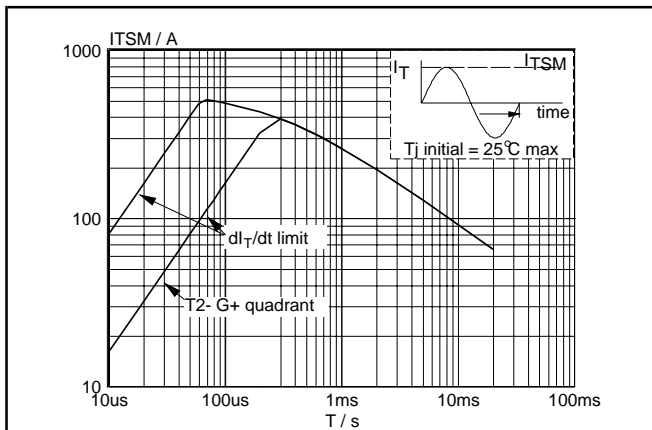


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \leq 20$ ms.

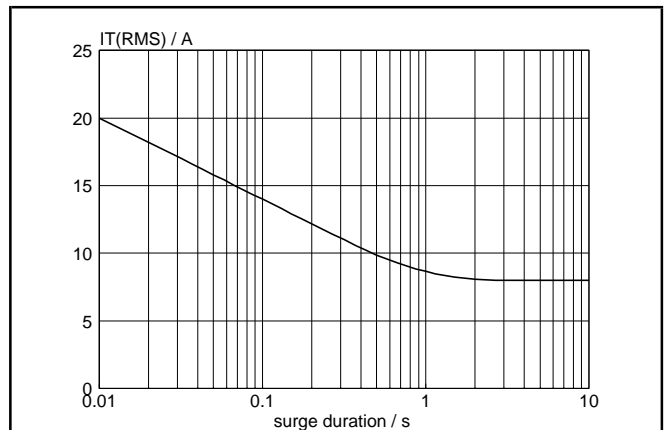


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents,  $f = 50$  Hz;  $T_{mb} \leq 102^\circ\text{C}$ .

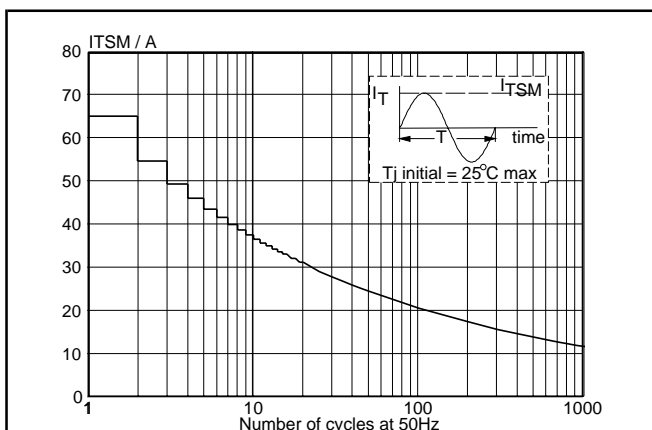


Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents,  $f = 50$  Hz.

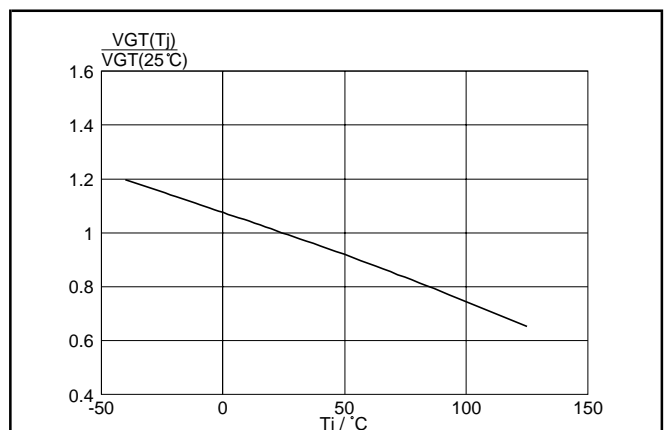
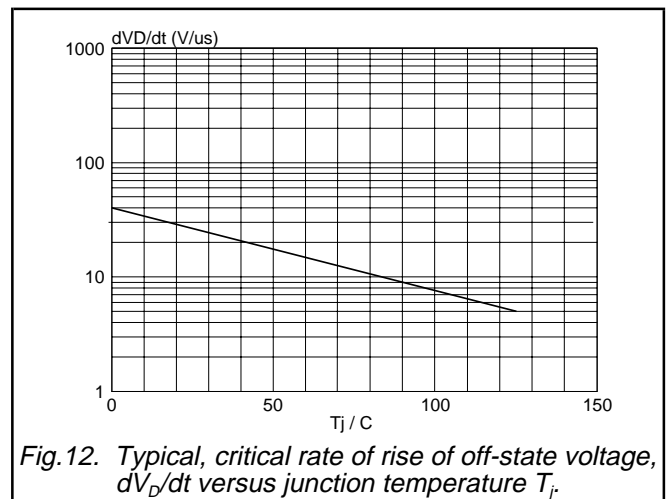
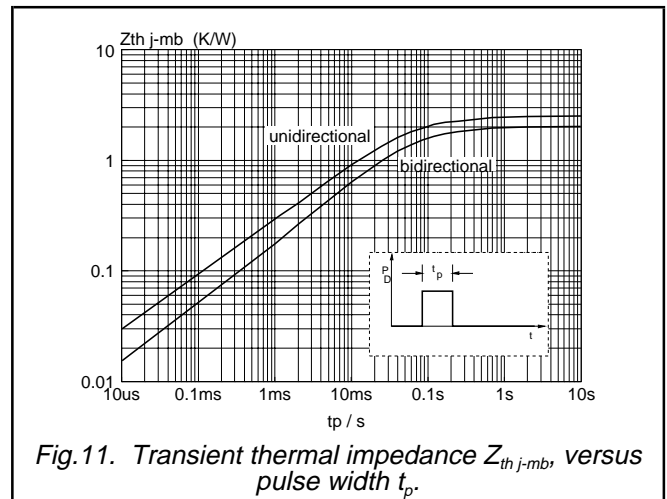
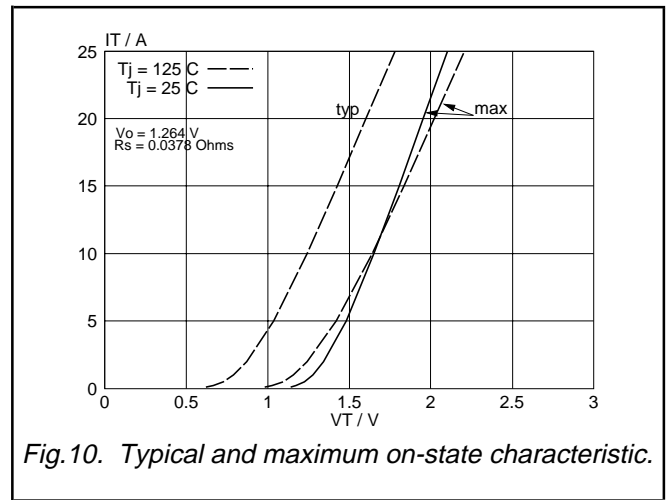
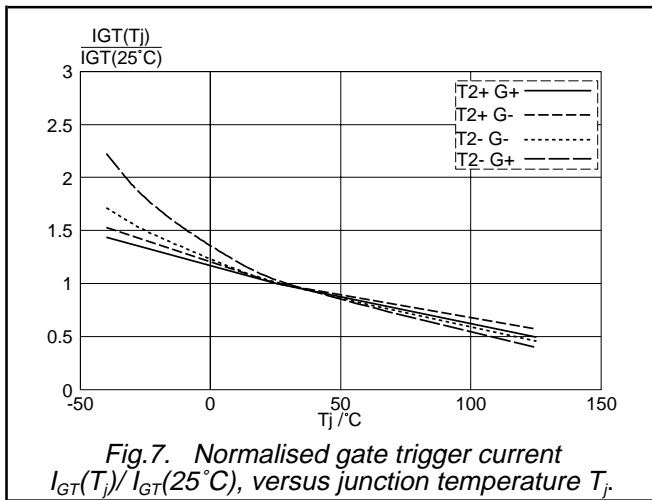


Fig.6. Normalised gate trigger voltage  $V_{GT}(T_j)/V_{GT}(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

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**MECHANICAL DATA**



**Notes**

- 1. Refer to mounting instructions for TO220 envelopes.
- 2. Epoxy meets UL94 V0 at 1/8".

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### DEFINITIONS

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	
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